ESD401 堅牢なIEC ESD性能を持つ1チャネルESD保護ダイオード

1 特長

- 堅牢なIEC 61000-4-2 レベル 4 ESD保護
  - 接触放電 ±24kV
  - 空気ギャップ放電 ±30kV
- IEC 61000-4-5 サージ保護
  - 4.5A (8/20µs)
  - 低いV_{clamp}: I_{PP} = 1.8Aで12V (8/20µs)
- IEC 61000-4-4 EFT保護
  - 80A (5/50ns)
- 双方向ESDダイオードにより最大±5.5Vまでインターフェイスを保護
- IO容量 0.77pF (標準値)
- 高いDCブレークダウン電圧: 8.3V (標準値)
- 非常に低い漏洩電流: 30pA (標準値)
- 低い動的抵抗: 0.7Ω (標準値)
- 工業用温度範囲: -40℃～+125℃
- 業界標準の0402パッケージ

2 アプリケーション

- 最終製品
  - ウェアラブル
  - ラップトップおよびデスクトップPC
  - モバイルおよびタブレット
  - セットトップ・ボックス
  - DVRおよびNVR
  - TVおよびモニタ
  - EPOS (電子販売時点情報管理)
- インターフェイス
  - 1Gbpsイーサネット
  - 5.5V許容のUSB 2.0/1.1
  - GPIO
  - プッシュボタン/キーパッド
  - オーディオ

3 概要

ESD401は双方向TVS ESD保護ダイオードで、低いR_{DYN}と低いクランピング電圧が特長です。ESD401は、IEC 61000-4-2国際規格で規定されている最大レベル(レベル4)を超えるESD耐性を備えています。動的抵抗が低い(0.7Ω)ため、過渡事象に対するシステム・レベルの保護が保証されます。このデバイスのIO容量は0.77pFで、USB 2.0などのインターフェイスを保護するために理想的です。このデバイスは、最大±5.5Vまで非常に低いリークで動作し、最大8.3VのDCフォルトに耐えられます。

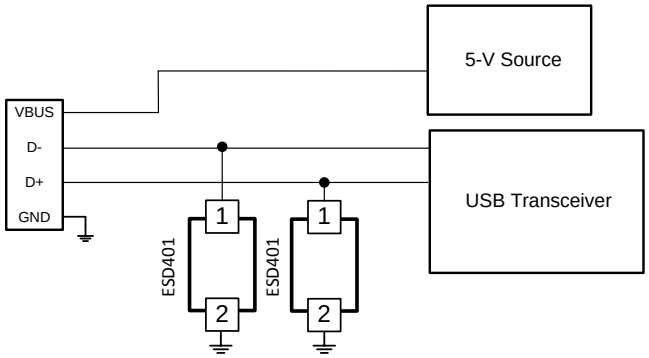
ESD401は、業界標準の0402 (DPY)パッケージで供給されます。

製品情報(1)

型番	パッケージ	本体サイズ(公称)
ESD401DPY	X1SON (2)	0.60mm×1.00mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

代表的なUSB 2.0アプリケーションの回路図



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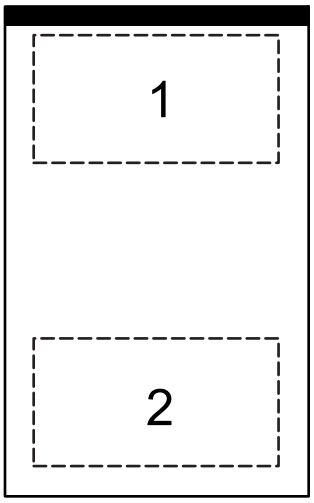
4 改訂履歴

2017年7月発行のものから更新 **Page**

- Updated 図 9 and図 13 ... 6

5 Pin Configuration and Functions

DPY Package
2-Pin X1SON
Top View



Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	IO	I/O	ESD Protected Channel. If used as ESD IO, connect pin 2 to ground
2	IO	I/O	ESD Protected Channel. If used as ESD IO, connect pin 1 to ground

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Electrical fast transient	IEC 61000-4-4 (5/50 ns) at 25°C		80	A
Peak pulse	IEC 61000-4-5 power (t_p - 8/20 µs) at 25°C		67	W
	IEC 61000-4-5 current (t_p - 8/20 µs) at 25°C		4.5	A
T_A	Operating free-air temperature	–40	125	°C
T_{stg}	Storage temperature	–65	155	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings — JEDEC Specification

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2500	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 ESD Ratings—IEC Specification

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	IEC 61000-4-2 contact discharge	±24000	V
		IEC 61000-4-2 air-gap discharge	±30000	

6.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{IO}	Input pin voltage	–5.5	5.5	V
T_A	Operating free-air temperature	–40	125	°C

6.5 Thermal Information

THERMAL METRIC(1)		ESD401 DPY (X1SON) 2 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	420	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	169.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	276.1	°C/W
ψ_{JT}	Junction-to-top characterization parameter	122.1	°C/W
ψ_{JB}	Junction-to-board characterization parameter	157.3	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.6 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{RWM}	Reverse stand-off voltage	I_{IO} < 10 nA	–5.5		5.5	V
V_{BRF}	Breakdown voltage, Pin 1 to Pin 2 (1)	I_{IO} =1 mA, at T_A = 25°C	7.5		9.1	V
V_{BRR}	Breakdown voltage, Pin 2 to Pin 1 (1)	I_{IO} =1 mA, at T_A = 25°C	7.5		9.1	V
V_{HOLD}	Holding voltage (2)	I_{IO} =1 mA		8.3		V
V_{CLAMP}	Clamping voltage	I_{PP} = 1 A, TLP, from Pin 1 to Pin 2 and Pin 2 to Pin 1, T_A = 25°C		11		V
		I_{PP} = 5 A, TLP, from Pin 1 to Pin 2 and Pin 2 to Pin 1, T_A = 25°C		16		
		I_{PP} = 16 A, TLP, from Pin 1 to Pin 2 and Pin 2 to Pin 1, T_A = 25°C		24		
		I_{PP} = 1.8 A, IEC-61000-4-5 (t_p - 8/20 µs) from Pin 1 to Pin 2 and Pin 2 to Pin 1, T_A = 25°C		12		
		I_{PP} = 4.5 A, IEC-61000-4-5 (t_p - 8/20 µs) from Pin 1 to Pin 2 and Pin 2 to Pin 1, T_A = 25°C		15		
I_{LEAK}	Leakage current, Pin 1 to Pin2 and PIn2 to Pin 1	V_{IO} = ±2.5 V		0.03	10	nA
R_{DYN}	Dynamic resistance	Measured between TLP I_{PP} of 10 A and 20 A, Pin 2 to Pin 1 and Pin 1 to Pin2, T_A = 25°C		0.7		Ω
C_L	Line capacitance	V_{IO} = 0 V, f = 1 MHz, Pin 1 to Pin 2 and Pin2 to Pin1, T_A = 25°C		0.77	0.95	pF

(1) V_{BRF} and V_{BRR} are defined as the voltage obtained at 1 mA when sweeping the voltage up, before the device latches into the snapback state.
(2) V_{HOLD} is defined as the voltage when 1 mA is applied, after the device has successfully latched into the snapback state.

6.7 Typical Characteristics

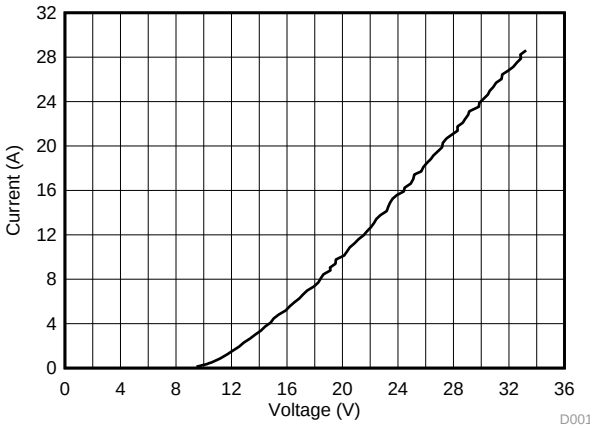


図 1. Positive TLP Curve, Pin 1 to Pin 2

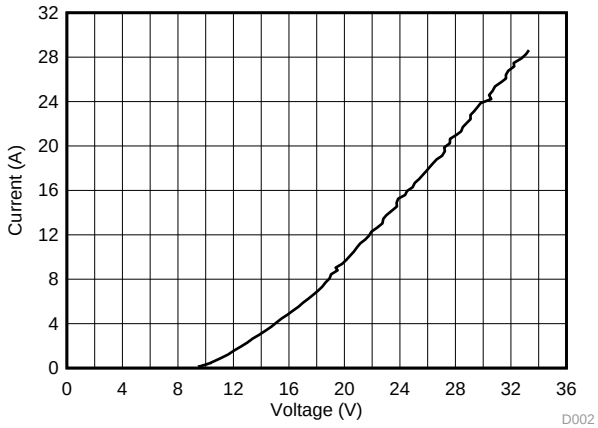


図 2. Negative TLP Curve, Pin 1 to Pin 2 (Plotted as Positive TLP Curve Pin 2 to Pin 1

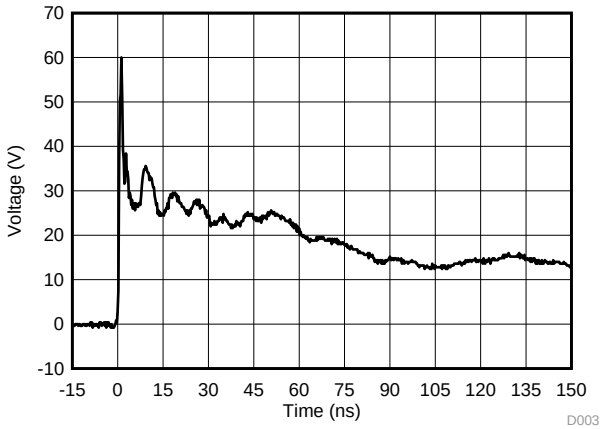


図 3. 8-kV IEC 61000-4-2 Waveform, Pin1 to Pin 2

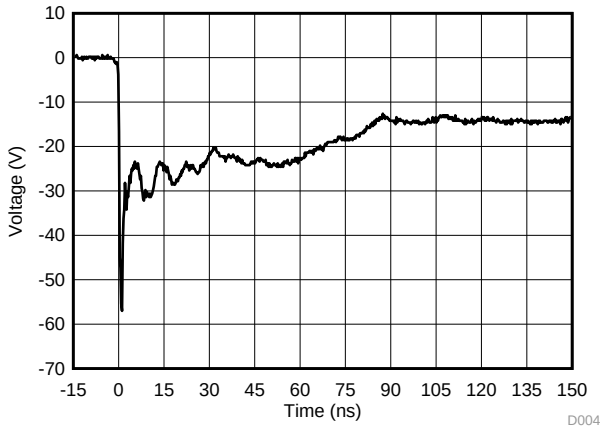


図 4. –8-kV IEC 61000-4-2 Waveform, Pin 1 to Pin 2

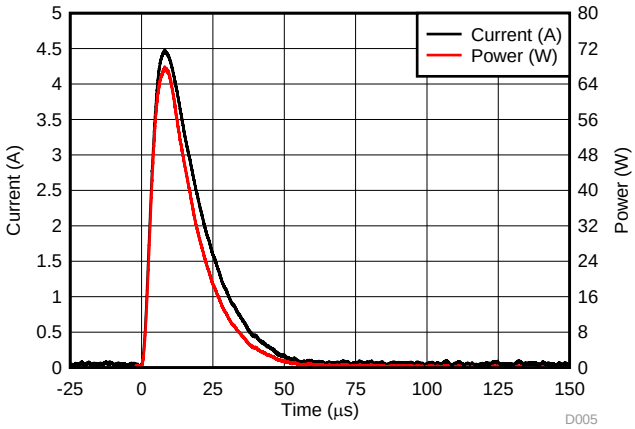


図 5. Surge (IEC 61000-4-5) Curve (tp = 8/20 µs), Pin 1 to Pin 2

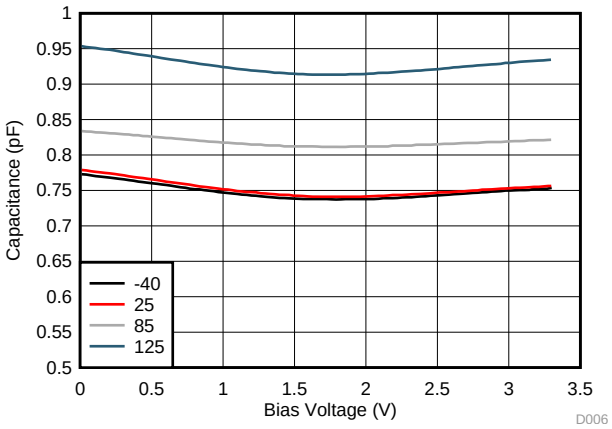


図 6. Capacitance vs Bias Voltage, Pin 1 to Pin 2

Typical Characteristics (continued)

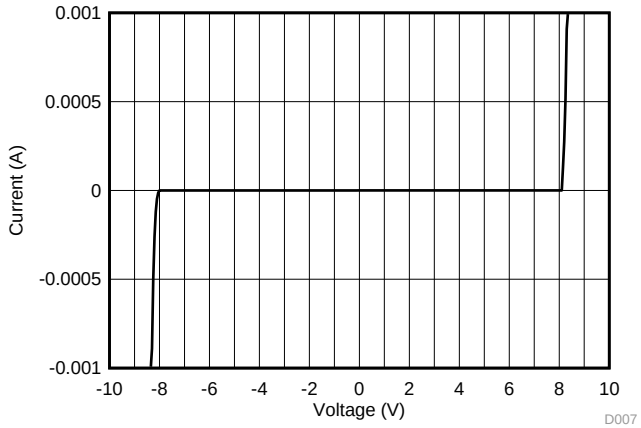


図 7. DC Voltage Sweep I-V Curve, Pin 1 to Pin 2

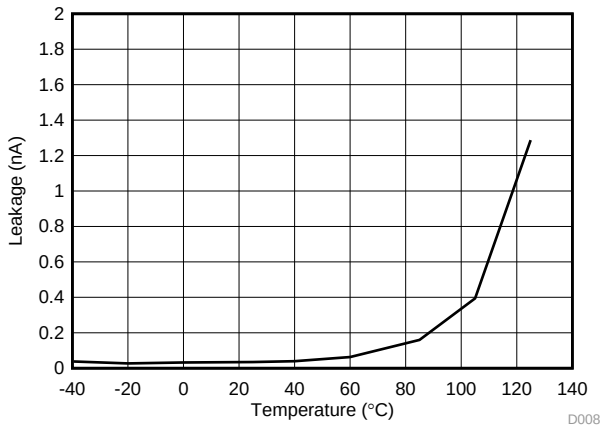


図 8. Leakage Current vs. Temperature, Pin 1 to Pin 2

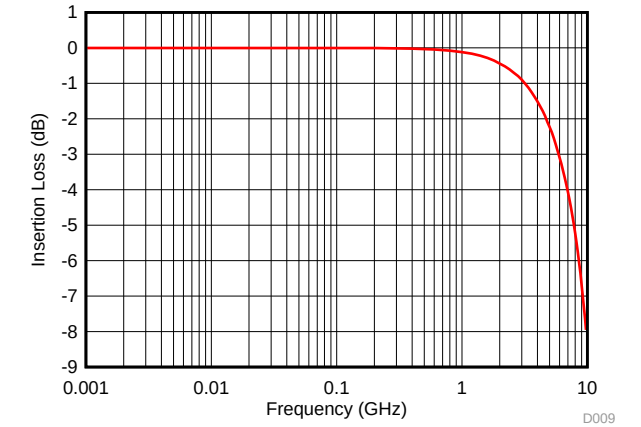


図 9. Insertion Loss

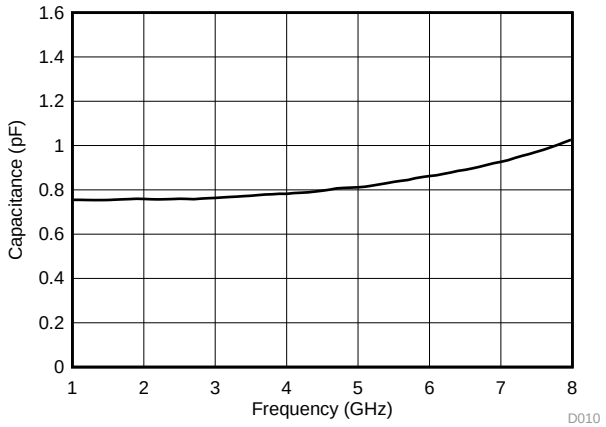


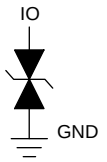
図 10. Capacitance vs. Frequency, Pin 1 to Pin 2

7 Detailed Description

7.1 Overview

The ESD401 is a bidirectional ESD Protection Diode with ultra-low clamping voltage. This device can dissipate ESD strikes above the maximum level specified by the IEC 61000-4-2 International Standard. The ultra-low clamping makes this device ideal for protecting any sensitive signal pins.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 IEC 61000-4-2 ESD Protection

The I/O pins can withstand ESD events up to ±24-kV contact and ±30-kV air gap. An ESD-surge clamp diverts the current to ground.

7.3.2 IEC 61000-4-4 EFT Protection

The I/O pins can withstand an electrical fast transient burst of up to 80 A (5/50 ns waveform, 4 kV with 50-Ω impedance). An ESD-surge clamp diverts the current to ground.

7.3.3 IEC 61000-4-5 Surge Protection

The I/O pins can withstand surge events up to 4.5 A and 67W (8/20 µs waveform). An ESD-surge clamp diverts this current to ground.

7.3.4 IO Capacitance

The capacitance between each I/O pin to ground is 0.77 pF (typical) and 0.95 pF (maximum).

7.3.5 DC Breakdown Voltage

The DC breakdown voltage of each I/O pin is ±8.3 V typical. This ensures that sensitive equipment is protected from surges above the reverse standoff voltage of ±5.5 V.

7.3.6 Low Leakage Current

The I/O pins feature an low leakage current of 10 nA (maximum) with a bias of ±2.5 V.

7.3.7 Low ESD Clamping Voltage

The I/O pins feature an ESD clamp that is capable of clamping the voltage to 24 V (TLP I_{PP} = 16 A).

7.3.8 Industrial Temperature Range

This device features an industrial operating range of –40°C to +125°C.

7.3.9 Industry Standard Footprint

The layout of this device makes it simple and easy to add protection to an existing layout. The packages offers flow-through routing, requiring minimal modification to an existing layout.

7.4 Device Functional Modes

The ESD401 is a passive integrated circuit that triggers when voltages are above V_{BRF} or below V_{BRR}. During ESD events, voltages as high as ±24 kV (contact) or ±30 kV (air) can be directed to ground via the internal diode network. When the voltages on the protected line fall below the trigger levels of ESD401 (usually within 10s of nano-seconds) the device reverts to passive.

図 11 shows typical TLP behavior of bi-directional ESD device that does not exhibit snapback.

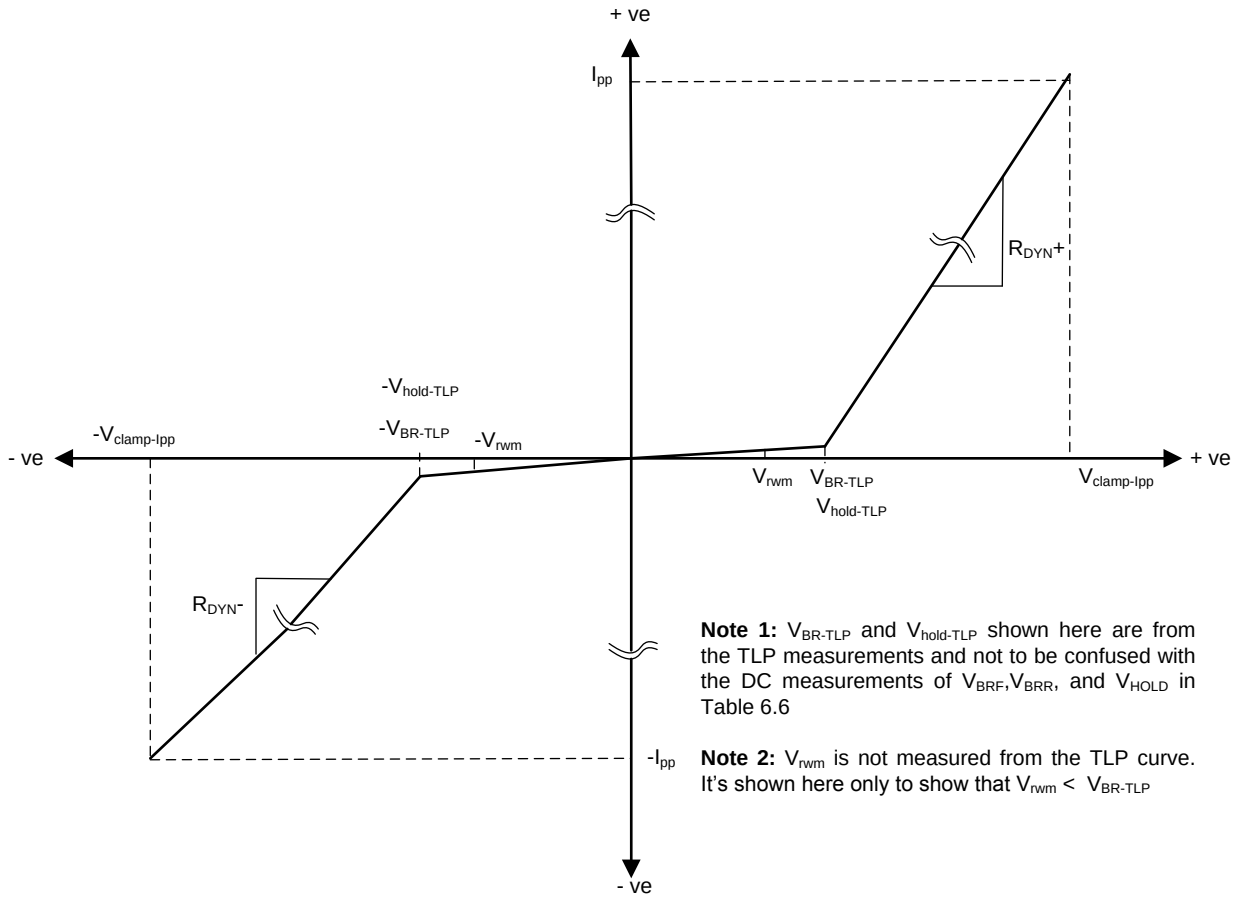


図 11. Typical TlpLP Behavior Of Bi-directional ESD Device that Does Not Exhibit Snapback

8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The ESD401 is a diode type TVS which is used to provide a path to ground for dissipating ESD events on high-speed signal lines between a human interface connector and a system. As the current from ESD passes through the TVS, only a small voltage drop is present across the diode. This is the voltage presented to the protected IC. The low R_{DYN} of the triggered TVS holds this voltage, V_{CLAMP}, to a safe level for the protected IC.

8.2 Typical Application

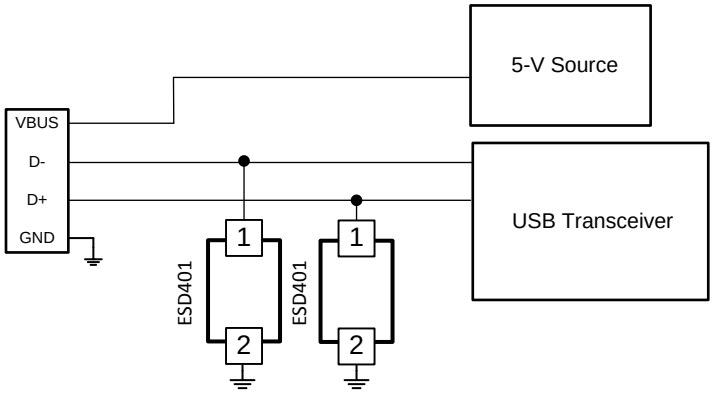


図 12. USB 2.0 ESD Schematic

8.2.1 Design Requirements

For this design example, two ESD401 devices are being used in a USB 2.0 application. This provides a complete ESD protection scheme.

Given the USB 2.0 application, the parameters listed in 表 1 are known.

表 1. Design Parameters

DESIGN PARAMETER	VALUE
Signal range on DP-DM lines	0 V to 3.6 V
Operating frequency on DP-DM lines	up to 240 MHz or 480 Mbps

8.2.2 Detailed Design Procedure

8.2.2.1 Signal Range

The ESD401 supports signal ranges between –5.5 V and 5.5 V, which supports the USB 2.0 signal range of 0 to 3.6 V on the DM/DP lines..

8.2.2.2 Operating Frequency

The ESD401 has a 0.85 pF (typical) capacitance, which supports the USB 2.0 data rates of 480 Mbps.

8.2.3 Application Curves

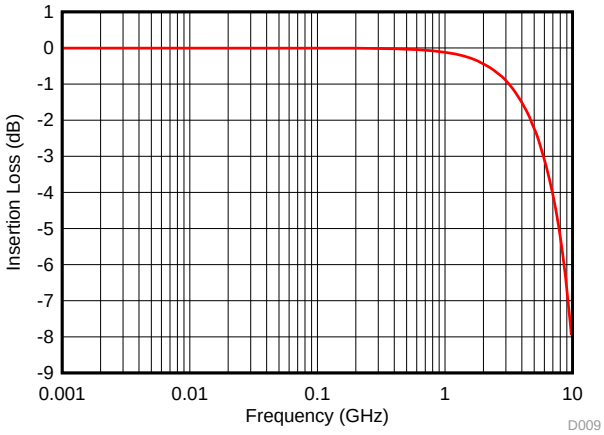


図 13. Insertion Loss

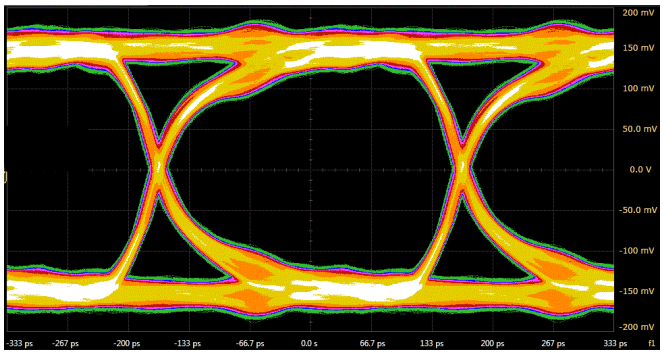


図 14. Eye Diagram - 3-Gbps Signal No Device

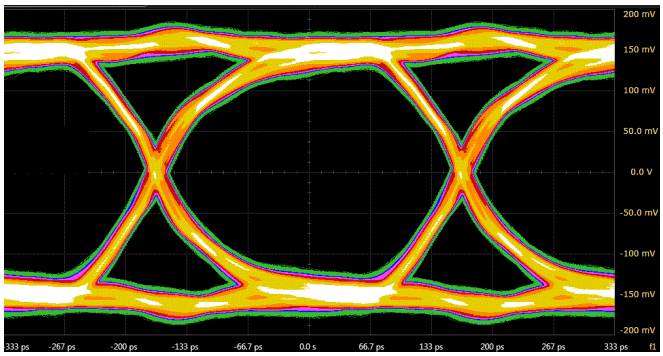


図 15. Eye Diagram - 3-Gbps Signal With ESD401

9 Power Supply Recommendations

The ESD401 is a passive ESD device so there is no need to power it. Take care not to violate the recommended I/O specification (–5.5 V to 5.5 V) to ensure the device functions properly.

10 Layout

10.1 Layout Guidelines

- The optimum placement is as close to the connector as possible.
  - EMI during an ESD event can couple from the trace being struck to other nearby unprotected traces, resulting in early system failures.
  - The PCB designer must minimize the possibility of EMI coupling by keeping any unprotected traces away from the protected traces which are between the TVS and the connector.
- Route the protected traces as straight as possible.
- Eliminate any sharp corners on the protected traces between the TVS and the connector by using rounded corners with the largest radii possible.
  - Electric fields tend to build up on corners, increasing EMI coupling.

10.2 Layout Example

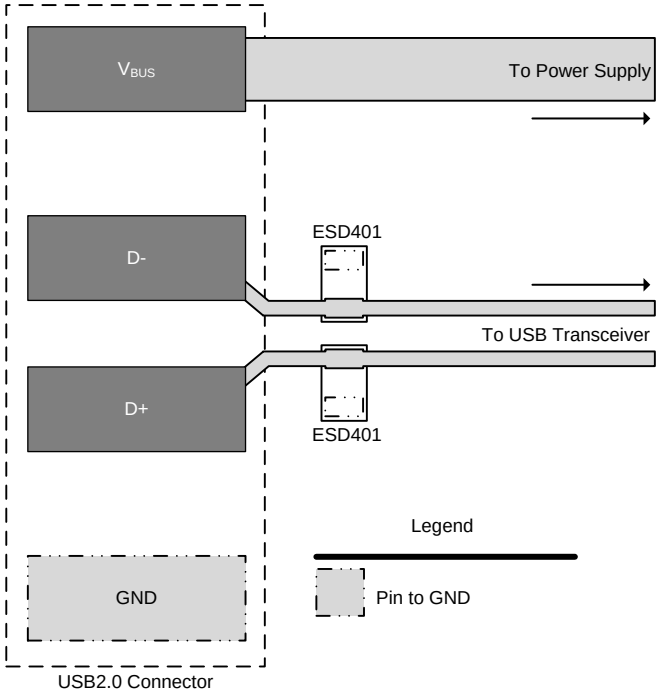


図 16. USB 2.0 ESD Layout

11 デバイスおよびドキュメントのサポート

11.1 ドキュメントのサポート

関連資料については、以下を参照してください。

『ESD401DPY評価モジュール』

11.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の隅にある「*通知を受け取る*」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

11.3 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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設計サポート ***TIの設計サポート*** **役に立つE2Eフォーラムや、設計サポート・ツールをすばやく見つけることができます。技術サポート用の連絡先情報も参照できます。**

11.4 商標

E2E is a trademark of Texas Instruments.

11.5 静電気放電に関する注意事項

すべての集積回路は、適切なESD保護方法を用いて、取扱いと保存を行うようにして下さい。

静電気放電はわずかな性能の低下から完全なデバイスの故障に至るまで、様々な損傷を与えます。高精度の集積回路は、損傷に対して敏感であり、極めてわずかなパラメータの変化により、デバイスに規定された仕様に適合しなくなる場合があります。

11.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ESD401DPYR	ACTIVE	X1SON	DPY	2	10000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8I	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

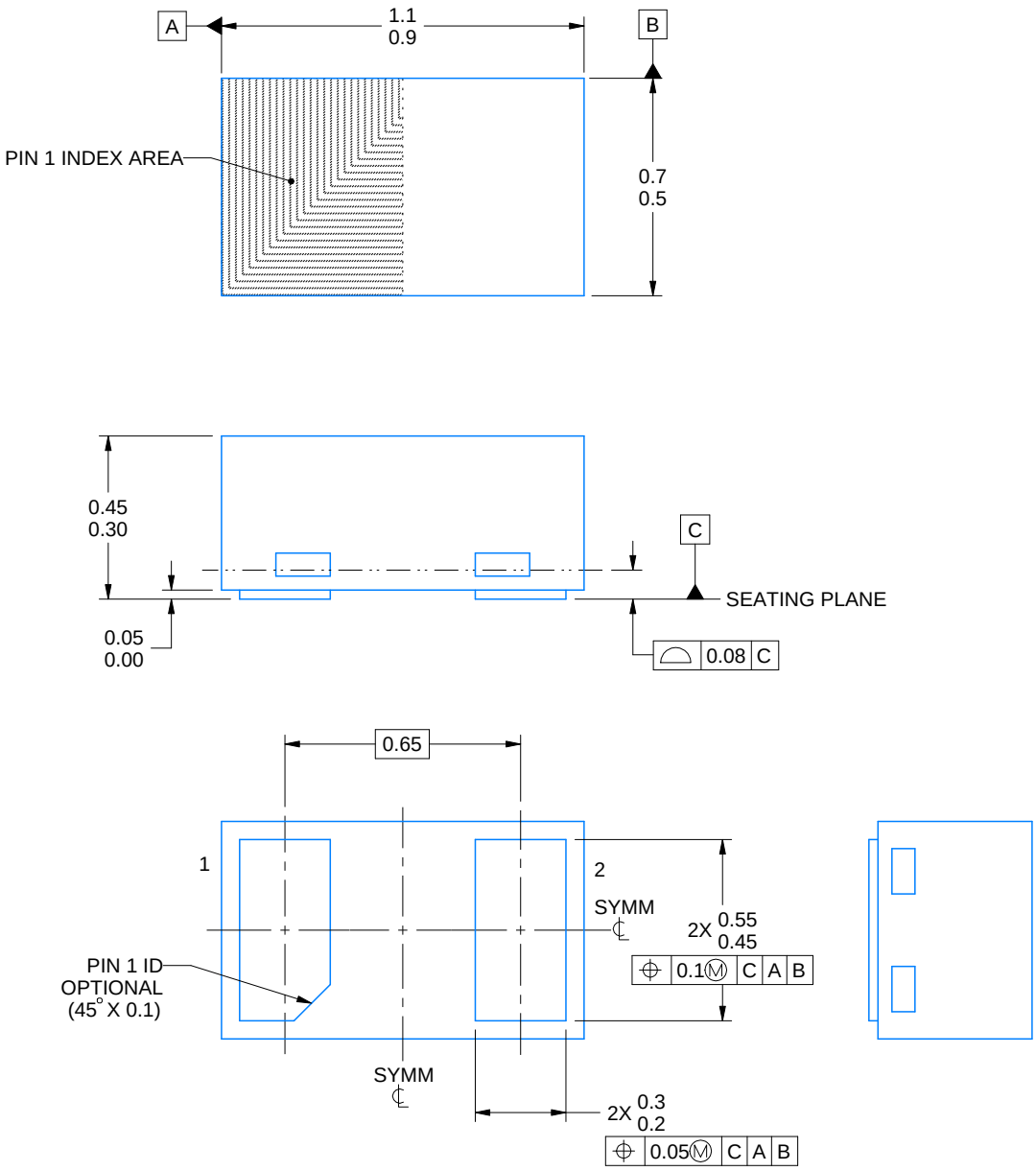
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

PACKAGE OUTLINE

DPY0002A

X1SON - 0.45 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



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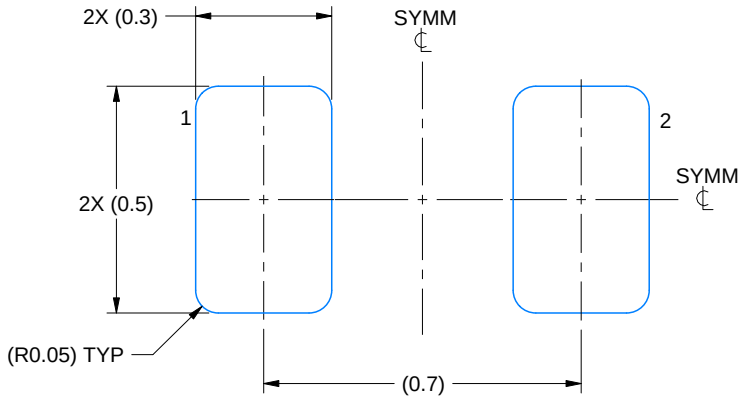
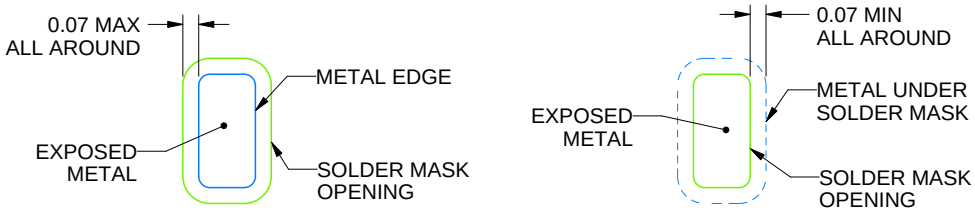
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:60X



SOLDER MASK DETAILS

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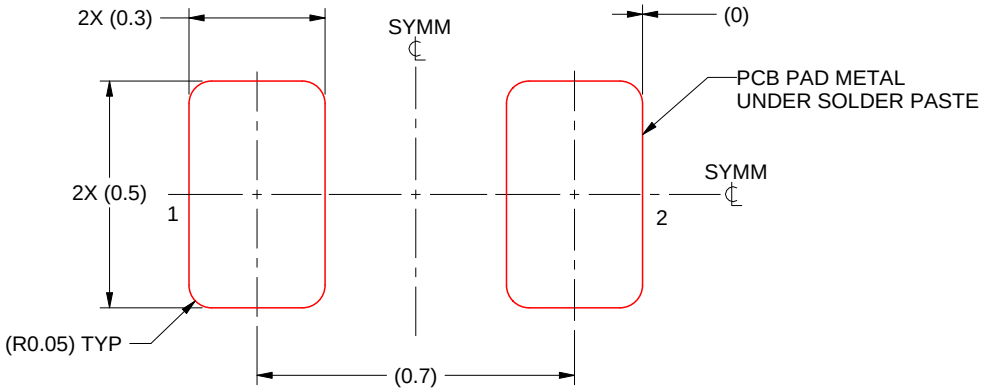
NOTES: (continued)

3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
4. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:60X

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NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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郵送先住所：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265